

Remarkable Rashba spin splitting induced by asymmetrical internal electric field in polar III-VI chalcogenides

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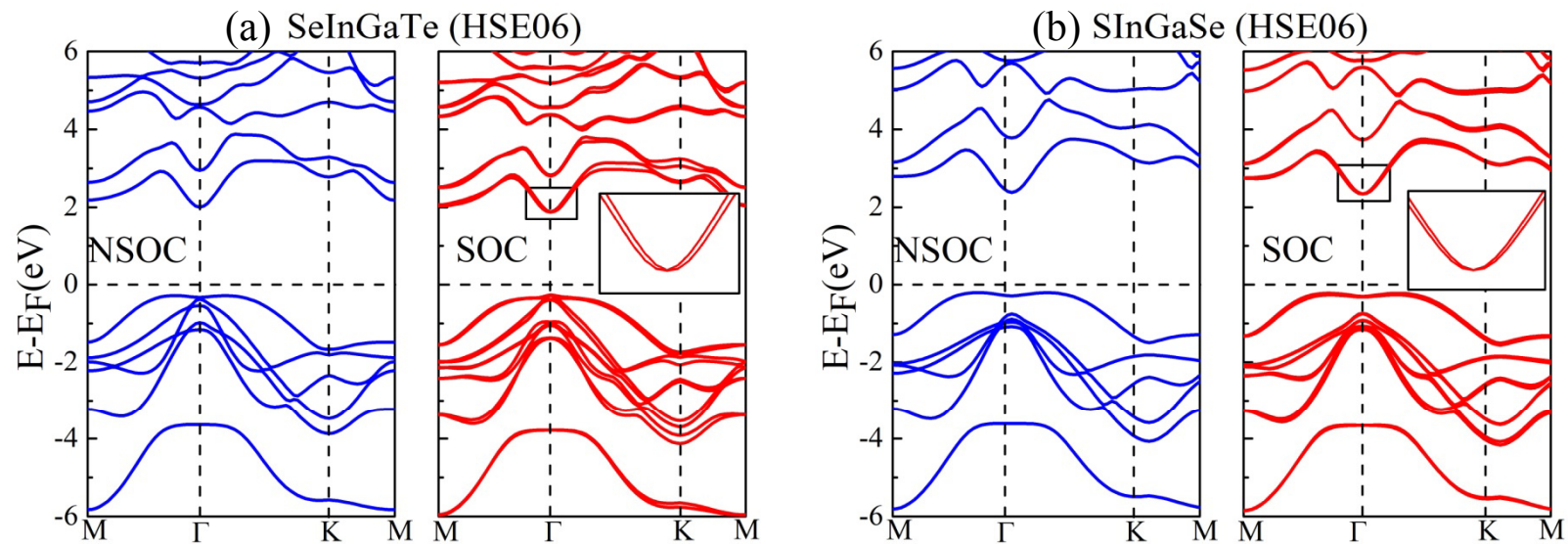
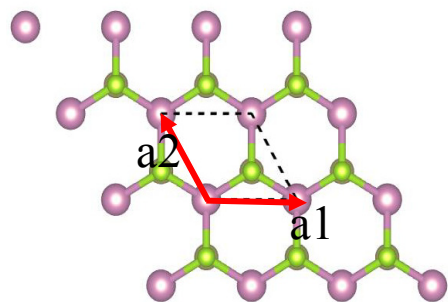
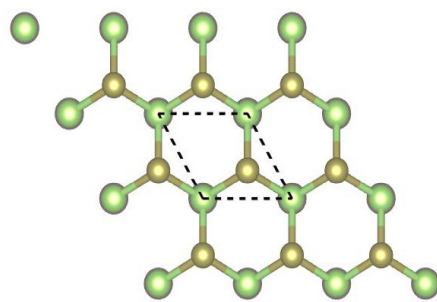


Fig. S1 Band structures of SeInGaTe and SInGaSe systems without SOC (blue lines) and with SOC (red lines) based on HSE06 hybrid functional method.

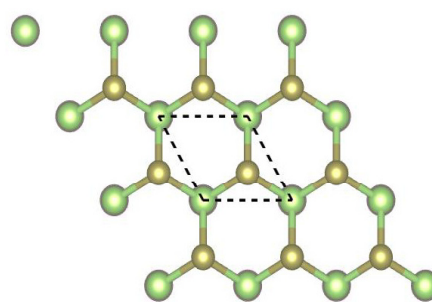
(a) SeInGaTe|SeInGaTe



(b) TeGaInSe|SeInGaTe



(c) TeGaGaTe|SeInGaTe



(d) TeGaGaTe|TeGaInSe

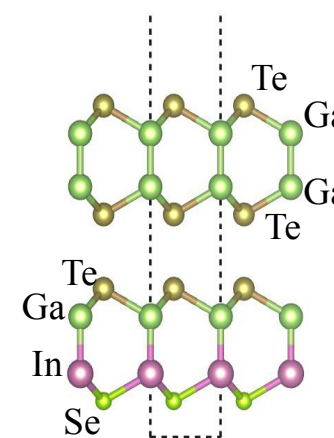
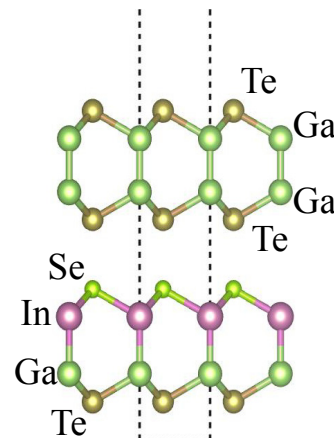
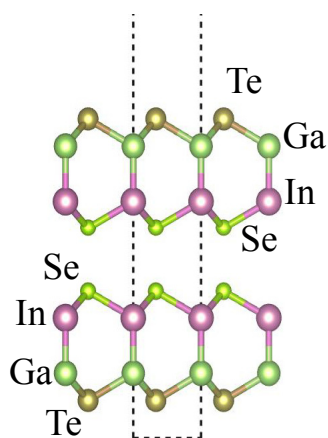
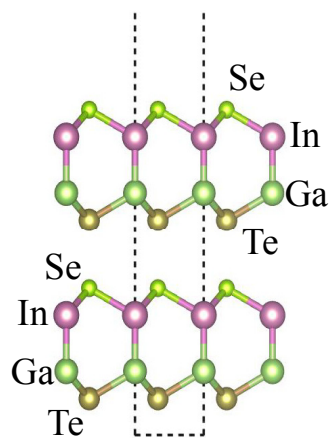
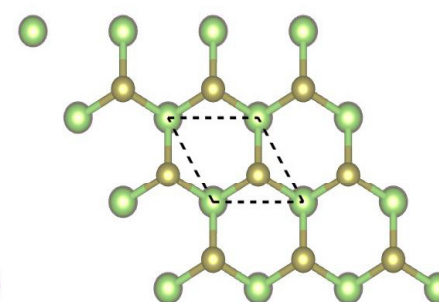


Fig. S2 The top and side view of SeInGaTe/SeInGaTe homostructure and SeInGaTe/GaTe heterostructure.